Memory Module Specifications

KVR26S19S6/8

8GB 1Rx16 1G x 64-Bit PC4-2666 CL19 260-Pin SODIMM

DESCRIPTION

This document describes ValueRAM's KVR26S19S6/8 as a 1G x 64-bit (8GB) DDR4-2666 CL19 SDRAM (Synchronous DRAM), 1Rx16, memory module, based on four 1G x 16-bit FBGA components. The SPD is programmed to JEDEC standard latency DDR4-2666 timing of 19-19-19 at 1.2V. This 260-pin SODIMM uses gold contact fingers. The electrical and mechanical specifications are as follows:

FEATURES

- Power Supply: VDD = 1.2V Typical
- VDDQ = 1.2V Typical
- VPP = 2.5V Typical
- VDDSPD = 2.2V to 3.6V
- Nominal and dynamic on-die termination (ODT) for data, strobe, and mask signals
- · Low-power auto self refresh (LPASR)
- Data bus inversion (DBI) for data bus
- On-die VREFDQ generation and calibration
- · Single-rank
- · On-board I2 serial presence-detect (SPD) EEPROM
- · 8 internal banks; 2 groups of 4 banks each
- Fixed burst chop (BC) of 4 and burst length (BL) of 8 via the mode register set (MRS)
- Selectable BC4 or BL8 on-the-fly (OTF)
- Fly-by topology
- Terminated control command and address bus
- PCB: Height 1.18" (30.00mm)
- · RoHS Compliant and Halogen-Free

SPECIFICATIONS

CL(IDD)	19 cycles
Row Cycle Time (tRCmin)	45.75ns(min.)
Refresh to Active/Refresh Command Time (tRFCmin)	350ns(min.)
Row Active Time (tRASmin)	32ns(min.)
()	02110(11111.)
UL Rating	94 V - 0
	· · · · ·
UL Rating	94 V - 0

Continued >>

MODULE DIMENSIONS



All measurements are in millimeters. (Tolerances on all dimensions are ±0.12 unless otherwise specified)



The product images shown are for illustration purposes only and may not be an exact representation of the product. Kingston reserves the right to change any information at anytime without notice.

©2020 Kingston Technology Corporation, 17600 Newhope Street, Fountain Valley, CA 92708 USA. All rights reserved. All trademarks and registered trademarks are the property of their respective owners.